Renesas Electronics America Inc - R5F21227KFP#U1 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	16MHz
Connectivity	CANbus, I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, Voltage Detect, WDT
Number of I/O	41
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21227kfp-u1

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Table 1.2 Functions and Specifications for R8C/23 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.4 Product Information for R8C/23 Group**
Peripheral Function	Ports	I/O ports: 41 pins, Input port: 3 pins
	Timers	Timer RA: 8 bits x 1 channel, Timer RB: 8 bits x 1 channel (Each timer equipped with 8-bit prescaler) Timer RD: 16 bits x 2 channel (Circuits of input capture and output compare) Timer RE: With compare match function
	Serial interface	1 channel (UART0) Clock synchronous I/O, UART 1 channel (UART1) UART
	Clock synchronous serial interface	1 channel I^2C bus interface(2), Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (Timer RA, UART0)
	CAN module	1 channel with 2.0B specification: 16 slots
	A/D converter	10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer	15 bits x 1 channel (with prescaler) Reset start selectable
	Interrupts	Internal: 14 sources, External: 6 sources, Software: 4 sources, Priority level: 7 levels
	Clock generation circuits	2 circuits XIN clock generation circuit (with on-chip feedback resistor) On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function.
	Oscillation stop detection function	Stop detection of XIN clock oscillation
	Voltage detection circuit	On-chip
	Power-on reset circuit include	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz)(D, J version) VCC = 3.0 to 5.5 V (f(XIN) = 16 MHz)(K version) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 12.5 mA (VCC = 5 V, f(XIN) = 20 MHz, High-speed on-chip oscillator stopping) Typ. 6.0 mA (VCC = 5 V, f(XIN) = 10 MHz, High-speed on-chip oscillator stopping)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	10,000 times (data flash)
		1,000 times (program ROM)
Operating Ambient Temperature		-40 to 85°C
		-40 to 125°C (option(1))
Package		48-pin mold-plastic LQFP

NOTES:
1. When using options, be sure to inquire about the specification.
2. I^2C bus is a registered trademark of Koninklijke Philips Electronics N.V.

2.8.7 Interrupt Enable Flag (I)

The I flag enables a maskable interrupt.
An interrupt is disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL, 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has greater priority than IPL, the interrupt is enabled.

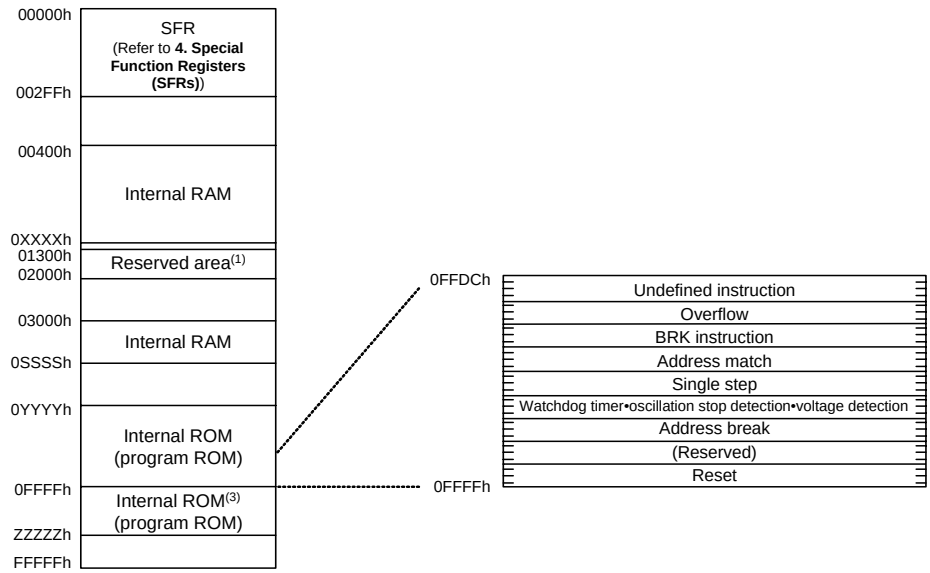
2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/22 Group

Figure 3.1 shows a Memory Map of R8C/22 Group. The R8C/22 Group has 1 Mbyte of address space from address 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFR) are allocated addresses 00000h to 002FFh and 01300h to 0147Fh (SFR area for CAN). The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future user and cannot be accessed by users.



NOTES:
1. SFR area for CAN is allocated addresses 01300h to 0147Fh.
2. The blank regions are reserved. Do not access locations in these regions.
3. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **24. Notes on Emulator Debugger**.

Part Number	Internal ROM			Internal RAM		
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0SSSSh
R5F21226DFP, R5F21226JFP, R5F21226KFP	32 Kbytes	08000h	-	2 Kbytes	00BFFh	-
R5F21227DFP, R5F21227JFP, R5F21227KFP	48 Kbytes	04000h	-	2.5 Kbytes	00DFFh	-
R5F21228DFP, R5F21228JFP, R5F21228KFP	64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	-
R5F2122AJFP, R5F2122AKFP	96 Kbytes	04000h	1BFFFh	5 Kbytes	00FFFh	037FFh
R5F2122CJFP, R5F2122CKFP	128 Kbytes	04000h	23FFFh	6 Kbytes	00FFFh	03BFFh

Figure 3.1 Memory Map of R8C/22 Group

Table 4.2 SFR Information (2)(1)

Address	Register	Symbol	After reset
0040h			
0041h			
0042h			
0043h	CAN0 Wake Up Interrupt Control Register	C01WKIC	XXXXX000b
0044h	CAN0 Successful Reception Interrupt Control Register	C0RECIC	XXXXX000b
0045h	CAN0 Successful Transmission Interrupt Control Register	C0TRMIC	XXXXX000b
0046h	CAN0 State/Error Interrupt Control Register	C01ERRIC	XXXXX000b
0047h			
0048h	Timer RD0 Interrupt Control Register	TRD0IC	XXXXX000b
0049h	Timer RD1 Interrupt Control Register	TRD1IC	XXXXX000b
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh			
004Ch			
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register/IIC Bus Interrupt Control Register(2)	SSUIC/IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh			
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. Selected by the IICSEL bit in the PMR register.

Table 4.7 SFR Information (7)(1)

Address	Register	Symbol	After reset
0180h			
0181h			
0182h			
0183h			
0184h			
0185h			
0186h			
0187h			
0188h			
0189h			
018Ah			
018Bh			
018Ch			
018Dh			
018Eh			
018Fh			
0190h			
0191h			
0192h			
0193h			
0194h			
0195h			
0196h			
0197h			
0198h			
0199h			
019Ah			
019Bh			
019Ch			
019Dh			
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h			
01B3h	Flash Memory Control Register 4	FMR4	01000000b
01B4h			
01B5h	Flash Memory Control Register 1	FMR1	1000000Xb
01B6h			
01B7h	Flash Memory Control Register 0	FMR0	00000001b
01B8h			
01B9h			
01BAh			
01BBh			
01FDh			
01FEh			
01FFh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.10 SFR Information (10)(1)

Address	Register	Symbol	After reset
1380h	CAN0 Slot 2: Identifier/DLC		XXh
1381h			XXh
1382h			XXh
1383h			XXh
1384h			XXh
1385h			XXh
1386h	CAN0 Slot 2: Data Field		XXh
1387h			XXh
1388h			XXh
1389h			XXh
138Ah			XXh
138Bh			XXh
138Ch			XXh
138Dh			XXh
138Eh	CAN0 Slot 2: Time Stamp		XXh
138Fh			XXh
1390h	CAN0 Slot 3: Identifier/DLC		XXh
1391h			XXh
1392h			XXh
1393h			XXh
1394h			XXh
1395h			XXh
1396h	CAN0 Slot 3: Data Field		XXh
1397h			XXh
1398h			XXh
1399h			XXh
139Ah			XXh
139Bh			XXh
139Ch			XXh
139Dh			XXh
139Eh	CAN0 Slot 3: Time Stamp		XXh
139Fh			XXh
13A0h	CAN0 Slot 4: Identifier/DLC		XXh
13A1h			XXh
13A2h			XXh
13A3h			XXh
13A4h			XXh
13A5h			XXh
13A6h	CAN0 Slot 4: Data Field		XXh
13A7h			XXh
13A8h			XXh
13A9h			XXh
13AAh			XXh
13ABh			XXh
13ACh			XXh
13ADh			XXh
13AEh	CAN0 Slot 4: Time Stamp		XXh
13AFh			XXh
13B0h	CAN0 Slot 5: Identifier/DLC		XXh
13B1h			XXh
13B2h			XXh
13B3h			XXh
13B4h			XXh
13B5h			XXh
13B6h	CAN0 Slot 5: Data Field		XXh
13B7h			XXh
13B8h			XXh
13B9h			XXh
13BAh			XXh
13BBh			XXh
13BCh			XXh
13BDh			XXh
13BEh	CAN0 Slot 5: Time Stamp		XXh
13BFh			XXh

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.11 SFR Information (11)(1)

Address	Register	Symbol	After reset
13C0h	CAN0 Slot 6: Identifier/DLC		XXh
13C1h			XXh
13C2h			XXh
13C3h			XXh
13C4h			XXh
13C5h			XXh
13C6h	CAN0 Slot 6: Data Field		XXh
13C7h			XXh
13C8h			XXh
13C9h			XXh
13CAh			XXh
13CBh			XXh
13CCh			XXh
13CDh			XXh
13CEh	CAN0 Slot 6: Time Stamp		XXh
13CFh			XXh
13D0h	CAN0 Slot 7: Identifier/DLC		XXh
13D1h			XXh
13D2h			XXh
13D3h			XXh
13D4h			XXh
13D5h			XXh
13D6h	CAN0 Slot 7: Data Field		XXh
13D7h			XXh
13D8h			XXh
13D9h			XXh
13DAh			XXh
13DBh			XXh
13DCh			XXh
13DDh			XXh
13DEh	CAN0 Slot 7: Time Stamp		XXh
13DFh			XXh
13E0h	CAN0 Slot 8: Identifier/DLC		XXh
13E1h			XXh
13E2h			XXh
13E3h			XXh
13E4h			XXh
13E5h			XXh
13E6h	CAN0 Slot 8: Data Field		XXh
13E7h			XXh
13E8h			XXh
13E9h			XXh
13EAh			XXh
13EBh			XXh
13ECh			XXh
13EDh			XXh
13EEh	CAN0 Slot 8: Time Stamp		XXh
13EFh			XXh
13F0h	CAN0 Slot 9: Identifier/DLC		XXh
13F1h			XXh
13F2h			XXh
13F3h			XXh
13F4h			XXh
13F5h			XXh
13F6h	CAN0 Slot 9: Data Field		XXh
13F7h			XXh
13F8h			XXh
13F9h			XXh
13FAh			XXh
13FBh			XXh
13FCh			XXh
13FDh			XXh
13FEh	CAN0 Slot 9: Time Stamp		XXh
13FFh			XXh

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/22 Group	100(3)	–	–	times
		R8C/23 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until erase suspend		–	–	97 + CPU clock × 6 cycle	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times.
   For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure endurance can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data Flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until erase suspend		–	–	97 + CPU clock × 6 cycle	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-40	–	85(8)	°C
–	Data hold time(9)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times.
   For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Minimum endurance to guarantee all electrical characteristics after program and erase (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times are the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure endurance can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. 125°C for K version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.9 High-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 V to 5.25 V, 0°C ≤ Topr ≤ 60°C(2)	39.2	40	40.8	MHz
		V_{CC} = 3.0 V to 5.25 V, -20°C ≤ Topr ≤ 85°C(2)	38.8	40	41.2	MHz
		V_{CC} = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 85°C(2)	38.4	40	41.6	MHz
		V_{CC} = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	38.0	40	42.0	MHz
		V_{CC} = 2.7 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	37.6	40	42.4	MHz
–	The value of the FRA1 register when the reset is deasserted		08h	40	F7h	–
–	High-speed on-chip oscillator adjustment range	Adjust the FRA1 register to -1 bit (the value when the reset is deasserted)	–	+ 0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when high-speed on-chip oscillator oscillating	V_{CC} = 5.0 V, Topr = 25°C	–	600	–	µA

NOTES:
1. V_{CC} = 2.7 V to 5.5 V, Topr = -40°C to 85°C (D, J version) / -40°C to 125°C (K version), unless otherwise specified.
2. The standard value shows when the reset is deasserted for the FRA1 register.

Table 5.10 Low-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		40	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when low-speed on-chip oscillator oscillating	V_{CC} = 5.0 V, Topr = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.7 V to 5.5 V, Topr = -40°C to 85°C (D, J version) / -40°C to 125°C (K version), unless otherwise specified.

Table 5.11 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), unless otherwise specified.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until CPU clock supply starts since the interrupt is acknowledged to exit stop mode.

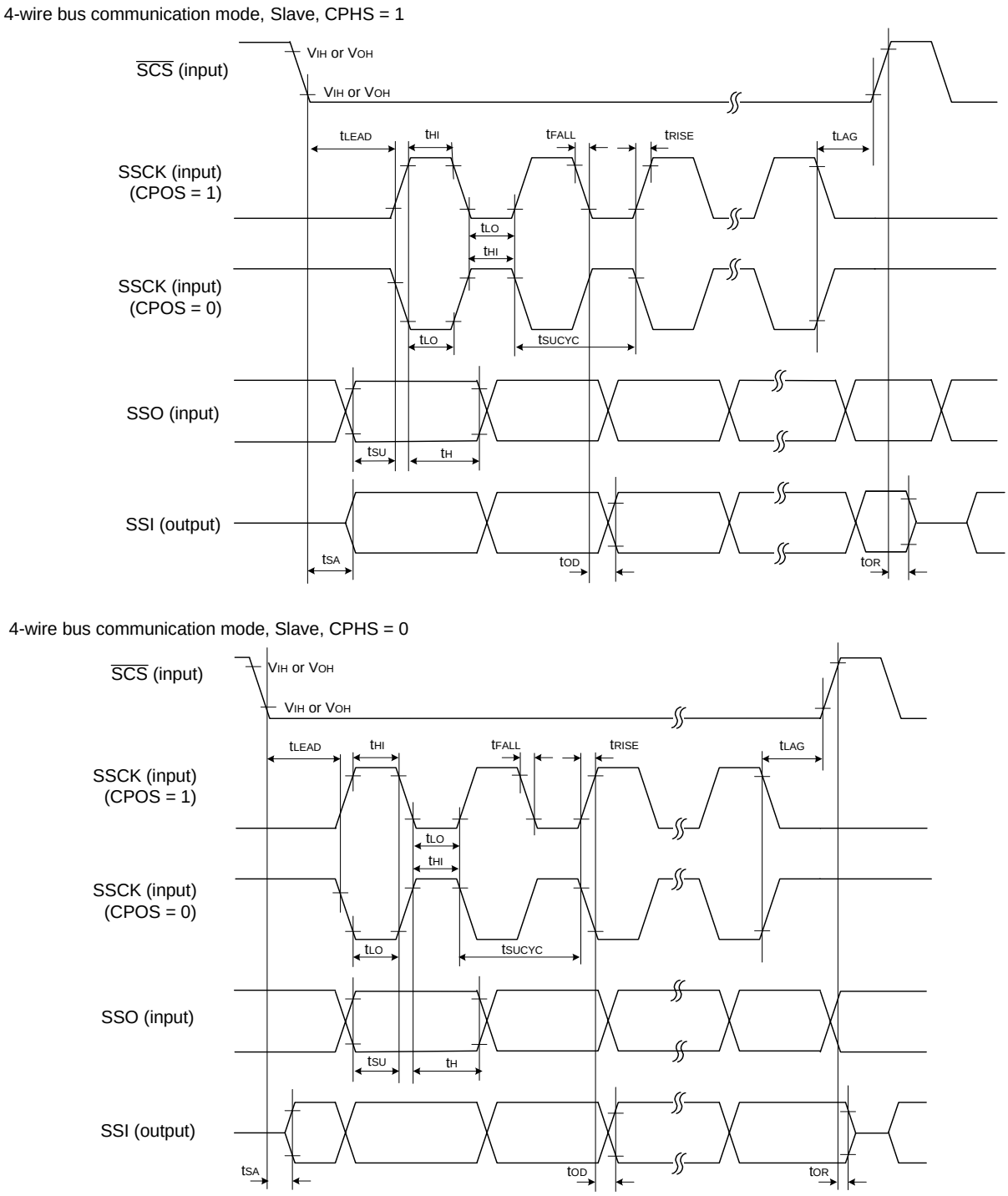
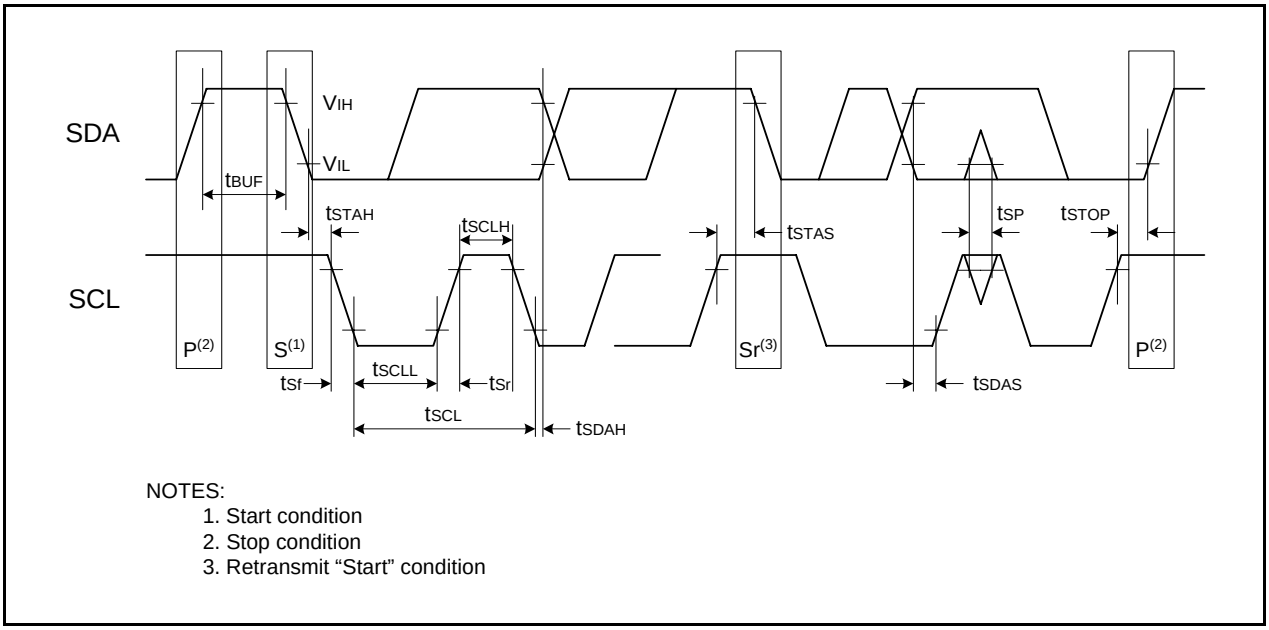


Figure 5.5 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

Table 5.13 Timing Requirements of I²C Bus Interface(1)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC}$ + 600(2)	–	–	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC}$ + 300(2)	–	–	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC}$ + 500(2)	–	–	ns
t_{sf}	SCL, SDA input falling time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	$1t_{CYC}$(2)	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}$(2)	–	–	ns
t_{STAH}	Start condition input hole time		$3t_{CYC}$(2)	–	–	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{SOAS}	Data input setup time		$1t_{CYC}$ + 20(2)	–	–	ns
t_{SDAH}	Data input hold time		0	–	–	ns

NOTES:
1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0V at Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)



NOTES:
1. Start condition
2. Stop condition
3. Retransmit “Start” condition

Figure 5.7 I/O Timing of I²C Bus Interface

Table 5.14 Electrical Characteristics (1) [Vcc = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” Voltage	Except XOUT	I_{OH} = -5 mA		Vcc – 2.0	–	Vcc	V
			I_{OH} = -200 μA		Vcc – 0.3	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	Vcc – 2.0	–	Vcc	V
			Drive capacity LOW	I_{OH} = -500 μA	Vcc – 2.0	–	Vcc	V
V_{OL}	Output “L” Voltage	Except XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, Vcc = 5 V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, Vcc = 5 V		–	–	-5.0	μA
R_{PULLUP}	Pull-Up Resistance		VI = 0 V, Vcc = 5 V		30	50	167	kΩ
R_{fXIN}	Feedback Resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM Hold Voltage		During stop mode		2.0	–	–	V

NOTE:
1. Vcc = 4.2 to 5.5 V at Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.15 Electrical Characteristics (2) [Vcc = 5 V]
(Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), Unless Otherwise Specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) In single-chip mode, the output pins are open and other pins are Vss	High-clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	12.5	25.0	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10.0	20.0	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6.5	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	6.5	–	mA
			XIN = 16MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5.0	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	6.5	13.0	mA
			XIN clock off High-speed on-chip oscillator on fOCO= 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.2	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	150	300	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA20 = 0 VCA26 = VCA27 = 0	–	60	120	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA20 = 0 VCA26 = VCA27 = 0	–	38	76	µA
		Stop mode Topr = 25°C	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA26 = VCA27 = 0	–	0.8	3.0	µA
		Stop mode Topr = 85°C	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA26 = VCA27 = 0	–	1.2	–	µA
		Stop mode Topr = 125°C	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA26 = VCA27 = 0	–	4.0	–	µA

Timing Requirements (Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Topr = 25°C) [Vcc = 5 V]

Table 5.16 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

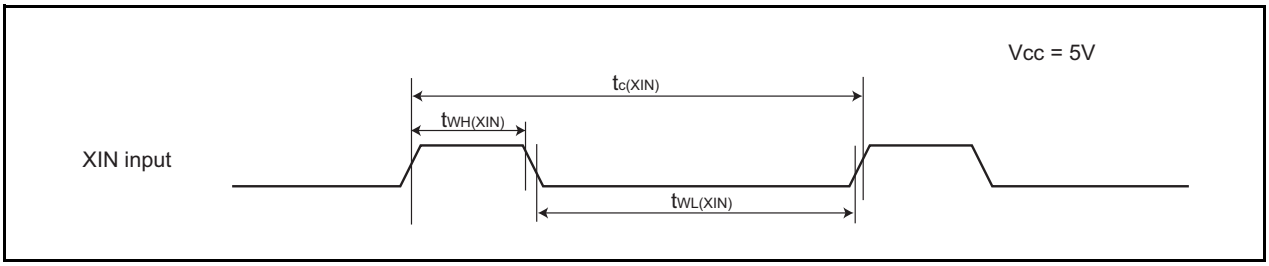


Figure 5.8 XIN Input Timing Diagram when Vcc = 5 V

Table 5.17 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

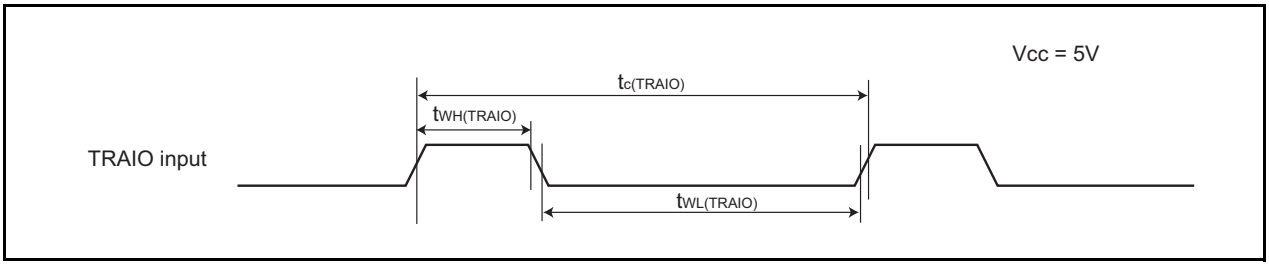
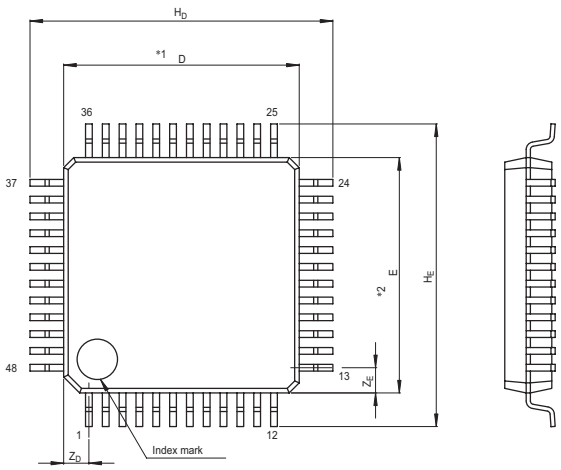


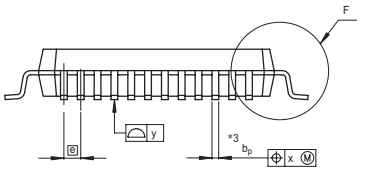
Figure 5.9 TRAIO Input Timing Diagram when Vcc = 5 V

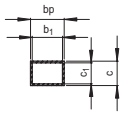
Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

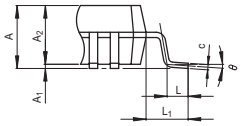
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP48-7x7-0.50	PLQP0048KB-A	48P6Q-A	0.2g







Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	R8C/22 Group, R8C/23 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Mar 08, 2005	–	First Edition issued
0.20	Sep 29, 2005	–	Words standardized - Clock synchronous serial interface → Clock synchronous serial I/O - Chip-select clock synchronous interface(SSU) → Clock synchronous serial I/O with chip select - I^2C bus interface(IIC) → I^2C bus interface
		2, 3	Table1.1 R8C/22 Group Performance, Table1.2 R8C/23 Group Performance Serial Interface revised: - Clock Synchronous Serial Interface: 1 channel I^2C bus Interface (3), Clock synchronous serial I/O with chip select - Power-On Reset Circuit added - Power Consumption value determined
		5, 6	Table 1.3 Product Information of R8C/22 Group, Table 1.4 Product Information of R8C/23 Group Date revised.
		7	Figure 1.4 Pin Assignment Pin name revised: - P3_5/$\overline{\text{SSC}}$K(/SCL) → P3_5/ SCL/$\overline{\text{SSC}}$K - P3_4/$\overline{\text{SCS}}$(/SDA) → P3_4/ SDA /$\overline{\text{SCS}}$ - VSS → VSS/AVSS - VCC → VCC/AVCC - P1_5/$\overline{\text{RXD0}}$/(TRAIO/$\overline{\text{INT1}}$) → P1_5/RXD0/(TRAIO)/($\overline{\text{INT1}}$) - P6_6/$\overline{\text{INT2}}$/(TXD1) → P6_6/$\overline{\text{INT2}}$/TXD1 - P6_7/$\overline{\text{INT3}}$/(RXD1) → P6_7/$\overline{\text{INT3}}$/RXD1 - NOTE2 added
		8	Table 1.5 Pin Description - Analog Power Supply Input: line added - I^2C Bus Interface (IIC) → I^2C Bus Interface - SSU → Clock Synchronous Serial I/O with Chip Select
		9	Table 1.6 Pin Name Information by Pin Number revised - Pin Number 1: (SCL) → SCL - Pin Number 2: (SDA) → SDA - Pin Number 9: VSS → VSS/AVSS - Pin Number 11: VCC → VCC/AVCC - Pin Number 26: (TXD1) → TXD1 - Pin Number 27: (RXD1) → RXD1
		15	Table 4.1 SFR Information (1) revised - 0013h: XXXXXX00b → 00h
		17	Table 4.3 SFR Information (3) revised - 00BCh: 0000X000b → 00h/0000X000b
		18	Table 4.4 SFR Information (4) revised - 00D6h: 00000XXXb → 00h - 00F5h: UART1 Function Select Register added
		19	Table 4.5 SFR Information (5) revised - 0104h: TRATR → TRA

REVISION HISTORY	R8C/22 Group, R8C/23 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Oct 27, 2006	40	Table 5.15 Electrical Characteristics (1) [VCC = 5 V] → Table 5.14 Electrical Characteristics (1) [VCC = 5 V] revised. RAM Hold Voltage, Min.; "1.8" → "2.0" corrected.
		41	Table 5.16 Electrical Characteristics (2) [Vcc = 5 V] → Table 5.15 Electrical Characteristics (2) [Vcc = 5 V] revised. Wait mode revised.
		44	Table 5.21 Electrical Characteristics (3) [VCC = 3 V → Table 5.20 Electrical Characteristics (3) [VCC = 3 V] revised. RAM hold voltage, Min.; "1.8" → "2.0" corrected.
		45	Table 5.22 Electrical Characteristics (4) [Vcc = 3 V] → Table 5.21 Electrical Characteristics (4) [Vcc = 3 V] revised. Wait mode revised.
1.10	Mar 16, 2007	–	D version products added. Relevant descriptions revised because of expanding products - Table 1.1 to 1.4 revised. - Figure 1.2 and 1.3 revised. - Figure 3.1 and 3.2 revised. - Table 5.1 to 5.15 revised. - Table 5.20 and 5.21 revised.
		15	Table 4.1 revised; 000Ah: "00XXX000b" → "00h", 000Fh: "00011111b" → "00X11111b"
		42	Table 5.17 and Figure 5.9 revised; "$\overline{\text{INT1}}$ input" deleted
		43	Table 5.19 and Figure 5.11 revised; "i = 0, 2, 3" → "i = 0 to 3"
		46	Table 5.23 and Figure 5.13 revised; "$\overline{\text{INT1}}$ input" deleted
		47	Table 5.25 and Figure 5.15 revised; "i = 0, 2, 3" → "i = 0 to 3"
2.00	Aug 20, 2008	–	"RENESAS TECHNICAL UPDATE" reflected: TN-16C-A172A/E
		5, 6	Table 1.3, Table 1.4 revised Figure 1.2, Figure 1.3; ROM number "XXX" added
		13, 14	Figure 3.1, Figure 3.2; "Expanding area" deleted
		23	Table 4.9 135Fh Address "XXXX0000b" → "00h"
		28	Table 5.2; NOTE2 revised
		30	Table 5.4; NOTE2 and NOTE4 revised
		31	Table 5.5; NOTE2 and NOTE5 revised
		32	Table 5.6; "td(Vdet1-A)" added, NOTE5 added Table 5.7; "td(Vdet2-A)" and NOTE2 revised, NOTE5 added
		33	Table 5.8; "trth" and NOTE2 revised, Figure 5.3 revised

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